

1. (Currently Amended) A method of fabricating a semiconductor Insulated-Gate Field-Effect Transistor (Gated-FET), comprising:

depositing a semiconductor thin film layer on a ~~first~~ thick insulator; and

forming a substantially rectangular channel region in said semiconductor thin film layer, said channel region lightly doped to form a resistive channel, said wherein the height of the channel height region comprising the entire thin film thickness; and

depositing a gate insulator layer above said channel region; and

depositing a gate material above said ~~first~~ gate insulator layer, said material forming a gate region above said channel region; and

optimizing said thin film properties, gate insulator properties and gate material properties such that said gate region further comprises:

a first voltage level that modulates said channel resistance to a substantially non-conductive state by fully depleting majority carriers from said channel region; and  
a second voltage level that modulates said channel resistance to a substantially conductive state by at least partially accumulating majority carriers near the gate insulator surface in said channel region.

2. (As Filed) The method of claim 1, wherein said semiconductor thin film layer comprises one of a single crystal Silicon, polycrystalline Silicon, re-crystallized Silicon, Silicon on Insulator, any other semiconductor material, and any other combination of semiconductor materials.

3. (Previously Amended) The method of claim 1, wherein said first and gate insulator layers

comprises one of an oxide layer, oxy-nitride layer, nitride layer, any other dielectric material, and any other combination of dielectric materials.

4. (As Filed) The method of claim 1, wherein said gate material comprises one of a heavily doped thin film poly Silicon layer, salicided heavily doped poly Silicon layer, refractory metal layer and a metal layer.

5. (As Filed) The method of claim 1, wherein optimizing said gate material properties is further comprised of selecting a gate material comprising:

a higher work function with respect to said thin film channel region work function, when said channel region is doped with N type dopant; and

a lower work function with respect to said thin film channel region work function, when said channel region is doped with P type dopant.

6. (Previously Amended) The method of claim 1, comprising forming a source region and a drain region on opposite sides of said substantially rectangular channel region in said semiconductor thin film layer, further comprised of:

doping said source region to a higher level than said channel region, said dopant type same as said channel region; and

doping said drain region to a higher level than said channel region, said dopant type same as said channel region; and

providing a conducting path from said source region to said drain region through said resistive channel region in the middle, said conducting path comprising the entire thickness of the

thin film layer.

7. (As Filed) The method of claim 1, wherein depositing said semiconductor thin film layer further comprises:

defining a surface voltage as  $\Phi_s = V_D - V_{FB} - T_G * Q_s / \epsilon_G$ ; and

defining a surface dopant level as  $N_s = D * \exp(q\Phi_s/kT)$ ; and

defining a first thickness as  $L_D = [\epsilon_s * kT / (q^2 N_s)]^{0.5}$ ; and

defining a second thickness as  $X_A = \sqrt{2} * L_D * [(N_s/D)^{0.5} - 1]$ ; and

defining a surface charge as  $Q_s = q * N_s * X_A / (1 + X_A / (\sqrt{2} * L_D))$ ; and

iteratively identifying the consistent set of values that satisfies said definitions; and

depositing a substantially uniform thickness  $T_s$  of said semiconductor thin film layer, wherein

said thickness  $T_s$  is greater than said second thickness  $X_A$ ;

where,  $V_D$  is power supply voltage level,  $\epsilon_s$  is channel semiconductor permittivity,  $\epsilon_G$  is gate insulator permittivity,  $T_G$  is gate insulator thickness,  $V_{FB}$  is gate material to semiconductor channel absolute flat band voltage,  $k$  is the Boltzmann's constant,  $T$  is the absolute temperature,  $q$  is electron charge and  $D$  is channel region doping level.

8. (As Filed) The method of claim 1, wherein depositing said semiconductor thin film layer further comprises:

defining a first thickness as  $X = \epsilon_s * T_G / \epsilon_G$ ; and

defining a second thickness as  $Y = [(2 * \epsilon_s * (V_{FB} - V_T)) / (q * D)]^{0.5}$ ; and

defining a third thickness as  $Z = (X^2 + Y^2)^{0.5} - X$ ; and

depositing a substantially uniform thickness  $T_s$  of said semiconductor thin film layer, wherein

said thickness  $T_S$  satisfies a thickness range approximately  $0.8*Z$  to  $1.2*Z$ ;

where,  $\epsilon_S$  is channel semiconductor permittivity,  $\epsilon_G$  is gate insulator permittivity,  $T_G$  is gate insulator thickness,  $V_{FB}$  is gate material to semiconductor channel absolute flat band voltage,  $V_T$  is channel region absolute threshold voltage,  $q$  is electron charge and  $D$  is channel region doping level.

9. (As Filed) The method of claim 1, wherein said gate insulator material comprises an oxide, said gate material comprises a heavily doped poly Silicon material with opposite type dopant to said channel region, and depositing said semiconductor thin film layer further comprises:

defining a first thickness as  $X = 3*T_{OX}$  (Angstroms) ; and

defining a second thickness as  $Y = 0.28/\sqrt{D}$  (Angstroms) ; and

defining a third thickness as  $Z = (X^2 + Y^2)^{0.5} - X$  (Angstroms) ; and

depositing a substantially uniform thickness  $T_S$  of said semiconductor thin film layer, wherein

said thickness  $T_S$  further satisfies a thickness range approximately  $0.8*Z$  to  $1.2*Z$ ;

where,  $T_{OX}$  is gate oxide thickness in Angstroms,  $D$  is channel doping level in atoms/(Angstroms)<sup>3</sup> and  $T_S$  is channel semiconductor layer thickness in Angstroms.

10. (As Filed) The method of claim 1, comprised of forming one of N channel or P channel Gated-FET thin film transistor consisting a process sequence comprised of:

depositing one of amorphous or crystalline poly-1 (P1);

performing P1 mask & etching P1;

applying blanket Gated-NFET  $V_T$  N- implant;

applying Gated-PFET  $V_T$  mask & P- implant;  
depositing Gox;  
depositing one of amorphous or crystalline poly-2 (P2);  
applying blanket P+ implantation of Gated-NFET Gate;  
applying N+ mask & implanting Gated-PFET Gate;  
applying P2 mask & etching P2;  
applying blanket LDN N implant (Gated-NFET LDD);  
applying LDP mask & P implant (Gated-PFET LDD);  
depositing a spacer oxide and etching the spacer oxide;  
depositing Nickel;  
salicidizing the Nickel on exposed P1 and P2;  
salicidizing P1 completely;  
performing RTA anneal, P1 and P2 re-crystallization and dopant anneal;  
depositing ILD oxide & CMP;  
applying C2 mask & etch;  
forming a W plug & CMP; and  
depositing M1.

11. (As Filed) The method of claim 1, comprised of forming one of N channel or P channel thinned down SOI Gated-FET thin film transistor consisting a process sequence comprised of:  
forming SOI substrate wafer;  
performing Shallow Trench isolation: Trench Etch, Trench Fill and CMP;  
depositing Sacrificial oxide;

applying Periphery PMOS  $V_T$  mask & implant;  
applying Periphery NMOS  $V_T$  mask & implant;  
applying Gated-FET mask and Silicon etch;  
performing Gated-FET blanket  $V_T$  N implant;  
applying Gated-FET  $V_T$  P mask and P implant;  
performing Dopant activation and anneal;  
performing Sacrificial oxide etch;  
depositing Gate oxide / Dual gate oxide option;  
depositing Gate poly (GP);  
applying Gated-FET N+ mask and N+ implant;  
applying Gated-FET P+ mask and P+ implant;  
applying GP mask & etch;  
applying LDN mask & N- implant;  
applying LDP mask & P- implant;  
depositing Spacer oxide & spacer etch;  
applying Periphery N+ mask and N+ implant;  
applying Periphery P+ mask and P+ implant;  
depositing Ni;  
performing RTA anneal - Ni salicidation (S/D/G regions & interconnect);  
performing Dopant activation;  
performing Unreacted Ni etch;  
depositing ILD oxide & CMP; and  
applying contact mask and etch.

12. (Previously Amended) The method of claim 6, wherein the absolute value of said channel region threshold voltage  $V_T$  comprises a value in the range from 0.10 to 0.40 times a system power voltage level, and preferably in the range 0.15 to 0.30 times a system power voltage level, and more preferably in the range 0.18 to 0.22 times a system power voltage level.

13. (Currently Amended) A method of fabricating a semiconductor N channel Gated-FET transistor, comprising:

depositing a semiconductor thin film layer on a first thick insulator; and

forming a substantially rectangular channel region in said semiconductor thin film layer, said

channel region lightly doped with N type dopant to form a resistive channel, ~~said~~ wherein

the height of the channel height region comprising the entire thin film thickness; and

forming a source region and a drain region on opposite sides of said rectangular channel region

in said semiconductor thin film layer, said source and drain regions heavily doped with N type dopant; and

depositing a gate insulator layer above said channel region; and

depositing a heavily P type doped poly-silicon gate material above said gate insulator layer, said

gate material forming a gate region above said channel region; and

optimizing said thin film properties, gate insulator properties and gate material properties such

that said gate region further comprises:

a first voltage level that modulates said channel resistance to a substantially non-

conductive state by fully depleting majority carriers from said channel region,

said state disconnecting said source from said drain region; and

a second voltage level that modulates said channel resistance to a substantially conductive state by at least partially accumulating majority carriers near the gate insulator surface of said channel region, said state connecting said source to said drain region.

14. (As Filed) The method of claim 13, wherein said first voltage level comprises a voltage in the range from system ground voltage level to a threshold voltage level, wherein: said thin film channel is fully depleted of majority carriers; and said source region is decoupled from said drain region for a drain to source differential bias voltage ranging from zero to a system power supply voltage.

15. (As Filed) The method of claim 13, wherein said second voltage level comprises a voltage in the range from said threshold voltage level to a flat band voltage level, wherein: said thin film channel is not fully depleted, said channel comprising majority carriers; and said source region is coupled to said drain region for a differential bias voltage ranging from zero to a system power supply voltage.

16. (As Filed) The method of claim 13, wherein said second voltage level comprises a voltage in the range from said flat band voltage level to a system power voltage level, wherein: said thin film channel majority carrier concentration is substantially enhanced above said channel doping level by an accumulation near the gate insulator surface; and said source region is coupled to said drain region for a differential bias voltage ranging from zero to a system power supply voltage.



17. (Currently Amended) A method of fabricating a semiconductor P-channel Gated-FET transistor, comprising:

depositing a semiconductor thin film layer on a ~~first~~ thick insulator; and

forming a substantially rectangular channel region in said semiconductor thin film layer, said

channel region lightly doped with P type dopant to form a resistive channel, ~~said wherein~~

the height of the channel height region comprising the entire thin film thickness; and

forming a source region and a drain region on opposite sides of said rectangular channel region

in said semiconductor thin film layer, said source and drain regions heavily doped with P type dopant; and

depositing a gate insulator layer above said channel region; and

depositing a heavily N type doped poly-silicon gate material above said gate insulator layer, said gate material forming a gate region above said channel region; and

optimizing said thin film properties, gate insulator properties and gate material properties such that said gate region further comprises:

a first voltage level that modulates said channel resistance to a substantially non-conductive state by fully depleting majority carriers from said channel region, said state disconnecting said source from said drain region; and

a second voltage level that modulates said channel resistance to a substantially conductive state by at least partially accumulating majority carriers near the gate insulator surface of said channel region, said state connecting said source to said drain region.

18. (As Filed) The method of claim 17, wherein said first voltage level comprises a voltage in the range from a system power voltage level to a threshold voltage below system power voltage level, wherein:

said thin film channel is fully depleted of majority carriers; and

said source region is decoupled from said drain region for a source to drain differential bias voltage ranging from zero to said system power supply voltage.

19. (As Filed) The method of claim 17, wherein said second voltage level comprises a voltage in the range from a flat band voltage level below system power voltage level to said threshold voltage below system power voltage level, wherein:

said thin film channel is not fully depleted, said channel comprising majority carriers; and

said source region is coupled to said drain region for a differential bias voltage ranging from zero to said system power supply voltage.

20. (As Filed) The method of claim 17, wherein said second voltage level comprises a voltage range from a system ground voltage level to said flat band voltage level below system power voltage level, wherein:

said thin film channel majority carrier concentration is substantially enhanced above said channel doping level by an accumulation near the gate insulator surface; and

said source region is coupled to said drain region for a differential bias voltage ranging from zero to said system power supply voltage.

Please amend page 24, paragraph 7 (starting at line 23) as follows:

For most practical doping levels and oxide thicknesses, ~~((X))~~ Y is much larger than ~~((Y))~~ X value. EQ-3 can be simplified to: